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#### **SDI Review Form 1.6**

Journal Name:	Physical Science International Journal
Manuscript Number:	Ms_PSIJ_29024
Title of the Manuscript:	Influence of Annealing Temperature on the Physical Properties of Polycrystalline Cu2SnSe3 Thin Films Prepared by Thermal Vacuum Evaporation Technique
Type of the Article	Original Research Article

#### General guideline for Peer Review process:

This journal's peer review policy states that <u>NO</u> manuscript should be rejected only on the basis of '<u>lack of Novelty'</u>, provided the manuscript is scientifically robust and technically sound.

To know the complete guideline for Peer Review process, reviewers are requested to visit this link:

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## PART 1: Review Comments

	Reviewer's comment	Author's comment (if agreed with reviewer, correct the manuscript and highlight that part in the manuscript. It is mandatory that authors should write his/her feedback here)
Compulsory REVISION	Title: "Influence of Annealing Temperature on the Physical Properties	
comments	of Polycrystalline Cu2SnSe3 Thin Films Prepared by Thermal Vacuum	
	Evaporation Technique" change to "Influence of Annealing Temperature on the	
	Physical Properties of Cu2SnSe3 Thin Films Prepared by Thermal Vacuum	
	Evaporation Technique".	
	If authors like to keep their interpretation, they must bring the details of the	
	Cu2SnSe3 Thin Films they used ("ref of bulk Cu2SnSe3" or "Spectre DRX"	
	with JCPDS or ICSD file numbers).	
	Section Abstract, Line 8) "p-type semiconductor". Specify the method	
	you used to confirm and please do not forget to add it in the text.	
	Section 3.2 Energy Dispersive X-Ray Analysis (EDX), Line 6) "Figure	
	5.26?" change to "Figure 3".	
	Section 3.2 Energy Dispersive X-Ray Analysis (EDX), Title of Figure	
	3) "Figure 3: EDX spectrum of Cu2SnSe3 thin films annealed at 500 °C."	
	change to "Figure 3: EDX spectrum of Cu2SnSe3 thin films as-deposited and	
	annealed (at 100, 200, 300, 400 and 500 ℃)."	
	How did you calculate the thickness for the deferent annealing	
	temperatures?	
	In addition to that:	

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	<ul> <li>First: See sections 3.3 I-V Characteristics, Please correct the design of figure 6.</li> </ul>
	- Secondly: See section 3.4 Electrical Resistivity and Conductivity,
	Please add the thickness (d) and the sheet resistance ( $R_s$ ) in table 2.
	- Third: please go to figure 7 and correct the symbol, instead of ( $\Omega$ ) you
	replace by electrical conductivity ( $\sigma$ ).
	<ul> <li>On the other hand I notice that the reference [15] did not exist in the</li> </ul>
	text.
Minor REVISION comments	<ul> <li>Section Abstract, Line 5) "Van der Pauw" change to "Van Der Pauw".</li> </ul>
	<ul> <li>Section Abstract, Line 9) "from I-V characteristic analysis" rephrase.</li> </ul>
	<ul> <li>Section 1. INTRODUCTION, Line 9) "mixed phase" change to "mixed</li> </ul>
	phases".
	<ul> <li>Section 1. INTRODUCTION, Line 9) "space group P n m a" change to</li> </ul>
	"space group Pnma".
	Section 1. INTRODUCTION, Line 13) "electrodeless" change to
	"electroless" or "electrodeposition". Please do not forget to add a reference.
Optional/General comments	<ul> <li>Specifiy the thickness and time of different annealing temperatures?</li> </ul>
	In my opinion, can you remove figure 1 or figure 2 because the
	comparaison for this study is not clear.

#### **Reviewer Details:**

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